

NPN Epitaxial Silicon Transistor

KSD526

Features

- Complement to KSB596
- This is a Pb-Free Device

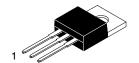
Applications

• Power Amplifier Applications

ABSOLUTE MAXIMUM RATINGS* (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Ratings	Units
V _{CBO}	Collector-Base Voltage	80	V
V _{CEO}	Collector-Emitter Voltage	80	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current	4	Α
Ι _Β	Base Current	0.4	Α
P _C	Collector Dissipation (T _C = 25°C)	30	W
TJ	T _J Junction Temperature		°C
T _{STG}	Storage Temperature	-55 ~ 150	°C

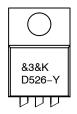
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



- 1. Base
- 2. Collector
- 3. Emitter

TO-220-3LD **CASE 340AT**

MARKING DIAGRAM



&3 = Date Code

&K = Lot Traceability Code D526-Y = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping
KSD526Y	TO-220-3LD (Pb-Free)	1200 Units / Bulk Bag
KSD526YTU	TO-220-3LD (Pb-Free)	1000 Units / Tube

KSD526/D

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may by impaired.

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ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Symbol	Characteristic	Test Condition	Min	Тур	Max	Unit
I _{CBO}	Collector Cut-off Current	V _{CB} = 80 V, I _E = 0			30	μΑ
I _{EBO}	Emitter Cut-off Current	V _{EB} = 5 V, I _C = 0			100	μΑ
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 50 \text{ mA}, I_B = 0$	80			V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 10 mA, I _C = 0	5			V
h _{FE}	DC Current Gain	V _{CE} = 5 V, I _C = 0.5 A V _{CE} = 5 V, I _C = 3 A	40 15	50	240	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 3 A, I _B = 0.3 A		0.45	1.5	V
V _{BE(on)}	Base-Emitter On Voltage	V _{CE} = 5 V, I _C = 3 A		1	1.5	V
f _T	Current Gain - Bandwidth Product	V _{CE} = 5 V, I _C = 0.5 A	3	8		MHz
C _{cb}	Collector Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1 MHz		90		pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

$h_{\mbox{\scriptsize FE}}$ CLASSIFICATION

Classification	R	0	Y
h _{FE}	40 ~ 80	70 ~ 140	120 ~ 240

KSD526

TYPICAL CHARACTERISTICS

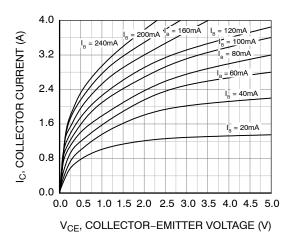


Figure 1. Static Characteristic

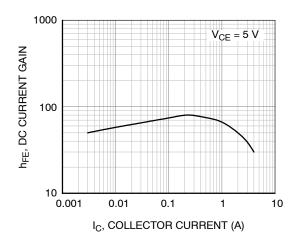


Figure 2. DC Current Gain

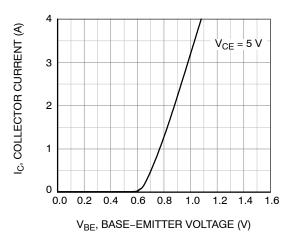


Figure 3. Base-Emitter On Voltage

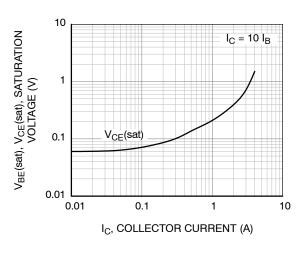


Figure 4. Collector-Emitter Saturation Voltage

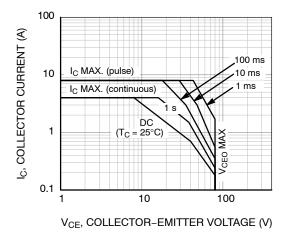


Figure 5. Safe Operating Area

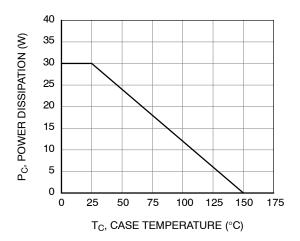
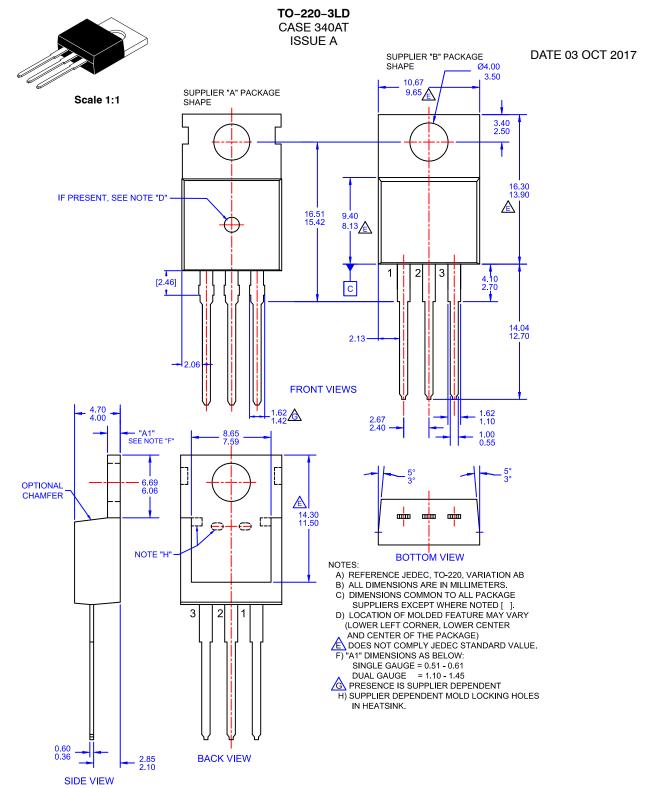


Figure 6. Power Derating



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